

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Jagdish Narayan
Application No.: 10/608,780 Group Art Unit: 2818
Filed: June 27, 2003 Examiner: Nhu, David
Confirmation No.: 8117
Title: DOMAIN EPITAXY FOR THIN FILM GROWTH



CERTIFICATE OF MAILING OR TRANSMISSION	
I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, or is being facsimile transmitted to the United States Patent and Trademark Office on:	
11-4-04 Date	<i>Jeanine Busby</i> Signature
Jeanine Busby Typed or printed name of person signing certificate	

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

11/09/2004 NROCHA1 00000034 10608780
02 FC:1806 180.00 OP

Sir:

This Information Disclosure Statement is submitted:

- ☐ under 37 CFR 1.129(a), or
(First/Second submission after Final Rejection)
- ☐ under 37 CFR 1.97(b), or
(Within any one of the following time periods: three months of filing national application (other than a CPA) or date of entry of the national stage in an international application; or before the mailing date of a first office action on the merits in a non-provisional application, including a CPA, or a Request for Continued Examination).
- ☒ under 37 CFR 1.97(c) together with either:
- ☐ a Statement under 37 CFR 1.97(e), as checked below, or
- ☒ a \$180.00 fee under 37 CFR 1.17(p), or
(After the 37 CFR 1.97(b) time period, but before final action or notice of allowance, whichever occurs first)
- ☐ under 37 CFR 1.97(d) together with:
- ☐ a Statement under 37 CFR 1.97(e), as checked below, and
- ☐ a \$180.00 fee under 37 CFR 1.17(p), or
(Filed after final action or notice of allowance, whichever occurs first, but on or before payment of the issue fee)
- ☐ under 37 CFR 1.97(i):
Applicant requests that the IDS and cited reference(s) be placed in the application filewrapper.
(Filed after payment of issue fee)

Statement Under 37 CFR 1.97(e)

- ☐ Each item of information contained in this Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement; or
- ☐ No item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the undersigned, after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of this Information Disclosure Statement.

Statement Under 37 CFR 1.704(d) (Patent Term Adjustment)

Applies to original applications (other than design) filed on or after May 29, 2000

- ☐ Each item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart application and this communication was not received by any individual designated in § 1.56(c) more than thirty days prior to the filing of the Information Disclosure Statement.
- ☒ Enclosed herewith is form PTO-1449:
 - ☒ Copies of the cited references AC8-AK8, AA9-AK9, AA10-AG10, AP6-AQ6, AL7-AQ7, AL8, AV6-AZ6 and AR7 are enclosed.
 - ☐ Since this application was filed after June 30, 2003, copies of issued U.S. patents and published U.S. applications are not required and are not being provided.
 - ☐ Copies of the cited references are enclosed except those entered in prior application, U.S. Application No. [], to which priority under 35 U.S.C. 120 is claimed. [The earlier application contains copies of the cited references.]
 - ☐ The listed references were cited in the enclosed International Search Report in a counterpart foreign application.
 - ☒ The "concise explanation" requirement (non-English references) for reference AQ6, AP7 and AQ7 under 37 CFR 1.98(a)(3) is satisfied by:
 - ☐ the explanation provided on the attached sheet.
 - ☐ the explanation provided in the Specification.
 - ☐ submission of the enclosed International Search Report.
 - ☐ submission of the enclosed English-language version of a foreign Search Report and/or foreign Office Action.
 - ☒ the enclosed English language abstract.

☐ Applicant requests that the following non-published pending applications be considered:

Examiner's
Initials

____ U.S. Patent Application No. [], by [inventor(s)], filed [], Docket No.: []
____ U.S. Patent Application No. [], by [inventor(s)], filed [], Docket No.: []
____ U.S. Patent Application No. [], by [inventor(s)], filed [], Docket No.: []

Examiner

Date

- ☐ A copy of each above-cited application, including the current claims, is enclosed.
- ☐ A copy of each above-cited application, including the current claims, is enclosed, except those entered in prior application, U.S. Application No. [], to which priority under 35 U.S.C. 120 is claimed.

The Examiner is requested to return a copy of the above list of pending applications indicating which references were considered with the next office communication.

It is requested that the information disclosed herein be made of record in this application.

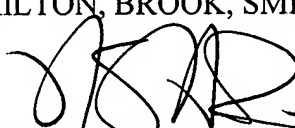
Method of payment:

- ☒ A check for the fee noted above is enclosed, or the fee has been included in the check with the accompanying Reply. A copy of this Statement is enclosed.
- ☐ Please charge Deposit Account 08-0380 in the amount of \$[]. A copy of this Statement is enclosed.
- ☒ Please charge any deficiency in fees and credit any overpayment to Deposit Account 08-0380.

Respectfully submitted,

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By


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Dated:

11/4/04

PTO-1449 REPRODUCED SUPPLEMENTAL INFORMATION DISCLOSURE CITATION IN AN APPLICATION November 4, 2004 (Use several sheets if necessary)	ATTORNEY DOCKET NO. 0717.2033-002		APPLICATION NO. 10/608,780	
	FIRST NAMED INVENTOR Jagdish Narayan		FILING DATE June 27, 2003	
	EXAMINER Nhu, David		CONFIRMATION NO. 8117	GROUP 2818

U.S. PATENT DOCUMENTS

EXAM- INER INI- TIAL	REF. NO.	DOCUMENT NUMBER Number-Kind Code (if known)	ISSUE DATE / PUBLICATION DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT
	AC8	6,495,862 B1	12-17-2002	Okazaki <i>et al.</i>
	AD8	US 2001/0032976 A1	10-25-2001	Ishikawa <i>et al.</i>
	AE8	US 2002/0001864 A1	01-03-2002	Ishikawa <i>et al.</i>
	AF8	US 2002/0182765 A1	12-05-2002	Tran <i>et al.</i>
	AG8	6,403,987 B1	06-11-2002	Miki <i>et al.</i>
	AH8	US2002/0047128 A1	04-25-2002	Song <i>et al.</i>
	AI8	6,344,665 B1	02-05-2002	Sung <i>et al.</i>
	AJ8	6,417,525 B1	07-09-2002	Hata
	AK8	5,760,423	06-02-1998	Kamakura <i>et al.</i>
	AA9	6,268,618 B1	07-31-2001	Miki <i>et al.</i>
	AB9	5,656,832	08-12-1997	Ohba <i>et al.</i>
	AC9	5,834,331	11-10-1998	Razeghi
	AD9	5,900,650	05-04-1999	Nitta
	AE9	6,153,894	11-28-2000	Udagawa
	AF9	6,118,801	09-12-2000	Ishikawa <i>et al.</i>
	AG9	6,521,999 B1	02-18-2003	Uemura <i>et al.</i>
	AH9	5,877,558	03-02-1999	Nakamura <i>et al.</i>
	AI9	5,455,195	10-03-1995	Ramsey <i>et al.</i>
	AJ9	6,531,383 B1	03-11-2003	Lee
	AK9	6,445,127 B1	09/03/2002	Oku, <i>et al.</i>
	AA10	6,410,942 B1	06-25-2002	Thibeault, <i>et al.</i>
	AB10	5,726,462	03-10-1998	Spahn, <i>et al.</i>
	AC10	6,060,335	05-09-2000	Rennie, <i>et al.</i>
	AD10	6,287,947 B1	09-11-2001	Ludowise, <i>et al.</i>
	AE10	5,442,205	08-15-1995	Brasen, <i>et al.</i>
	AF10	5,637,530	06-10-1997	Gaines, <i>et al.</i>

EXAMINER	DATE CONSIDERED
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(Use several sheets if necessary)

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PTO-1449 REPRODUCED SUPPLEMENTAL INFORMATION DISCLOSURE CITATION IN AN APPLICATION November 4, 2004 (Use several sheets if necessary)	ATTORNEY DOCKET NO. 0717.2033-002		APPLICATION NO. 10/608,780	
	FIRST NAMED INVENTOR Jagdish Narayan		FILING DATE June 27, 2003	
	EXAMINER Nhu, David		CONFIRMATION NO. 8117	GROUP 2818

FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER Country Code-Number-Kind Code (if known)	DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT	TRANSLATION YES NO	
	AP6	EP 0 513 745 A2	11-19-1992	CSELT Centro Studi e Laboratori Telecomunicazioni S.p.A.		
	AQ6	WO 01/73858 A1	10-04-2001	Toyoda Gosei Co., Ltd.		X
	AL7	WO 01/47038 A1	06-28-2001	Lumileds Lighting		
	AM7	WO 02/09185 A1	01-31-2002	American Xtal Technology, Inc.		
	AN7	EPO 622 858 A2	11-02-1994	Nichia Chemical Industries, Ltd.		
	AO7	EP 1 168 460 A2	01-02-2002	Kabushiki Kaisha Toshiba		
	AP7	DE 100 60 439 A	06-13-2002	OSRAM Opto Semiconductors GmbH & Co.		X
	AQ7	DE 199 34 031 A	05-04-2000	Industrial Technology Research Institute		X
	AL7	JP 2001 015811 A (abstract)	01-19-2001	Toyoda Gosei Co. Ltd.		

EXAMINER	DATE CONSIDERED
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	EXAMINER Nhu, David		CONFIRMATION NO. 8117	GROUP 2818

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
AV6	Chichibu, S., <i>et al.</i> , "Exciton Localization in InGaN Quantum Well Devices," <i>J. Vac. Sci. Technol B.</i> , Vol. 16(4):2204-2214 (1998).	
AW6	Chen, L., <i>et al.</i> , "Fabrication of 50-100 nm Patterned InGaN Blue Light Emitting Heterostructures," <i>IEEE, 14th Annual Meeting of the IEEE Lasers & Electro-Optics Society</i> , 1:760-761 (2001).	
AX6	Cho, H. K., <i>et al.</i> , "Influence of Strain-Induced Indium Clustering on Characteristics of InGaN/GaN Multiple Quantum Wells with High Indium Composition," <i>Journal of Applied Physics</i> , 91(3):1104-1107 (2002).	
AY6	Narayan, J. and H. Wang, "Effect of Thickness Variation in High-Efficiency InGaN/GaN Light-Emitting Diodes," <i>Applied Physics Letters</i> , 81(5): 841-843 (2002).	
AZ6	Kim, H., <i>et al.</i> , "Design and Fabrication of Highly Efficient GaN-Based Light-Emitting Diodes," <i>IEEE Transactions on Electron Devices</i> , 49(10):1715-1722 (2002).	
AR7	Maeda, T., <i>et al.</i> , "Effects of NiO on Electrical Properties of NiAu-Based Ohmic Contacts for <i>p</i> -type GaN," <i>Applied Physics Letters</i> 75(26):4145-4147 (1999).	

EXAMINER	DATE CONSIDERED
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